

Form PTO-1449	LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if Necessary)	ATTY. DOCKET NO. JG00060	SERIAL NO.
Ramdani et al.			
FILING DATE		GROUP	

JC006 U.S. PTO
 09/721566
 11/22/00

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>SK</i>	AW	6 1 0 3 0 0 8	8/15/00	McKee et al.	117	2	7/30/98
<i>SK</i>	AX	5 2 2 5 0 3 1	7/6/93	McKee et al.	156	612	4/10/91
	AY						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	GRANT DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES NO
	AZ 9 9 1 4 8 0 4	3/25/99	PCT	H01L	21/258	X

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>SK</i>	BA	"Formation of Si Epi./MgO-Al ₂ O ₃ Epi./SiO ₂ /Si and Its Epitaxial Film Quality," Masao Mikami et al., Fundamental Research Laboratories and Microelectronics Laboratories, pp. 31-34.
	BB	"An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF ₂ and Silicon," T. Asano et al., Graduate School of Science and Engineering, Tokyo Institute of Technology, pp. 143-151.
	BC	"Reaction and Regrowth Control of CeO ₂ on Si(111) Surface for the Silicon-On-Insulator Structure," T. Chikyow et al., Appl. Phys. Lett. 65(8), 22 August 1994, pp. 1030-1032.
	BD	"Epitaxial Growth of CeO ₂ (100) Films on Si(100) Substrates by Dual Ion Beams Reactive Sputtering," J.F. Kang et al., Solid State Communications, Vol. 108, No. 4, pp. 225-227.
	BE	"Vertical-Cavity Surface-Emitting Lasers Come of Age," Robert A. Morgan et al., SPIE, Vol. 2683, pp. 18-29.
	BF	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone(Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.
	BG	"Properties of GaAs Si Grown by Molecular Beam Epitaxy," R. Houdre et al., Solid State and Molecular Sciences, 1990, pp. 91-114.
<i>✓</i>	BH	"Gallium Arsenide and Other Compound Semiconductors on Silicon," S.F. Fang et al., J. Appl. Phys. 68(7), 1 October 1990, pp. R31-R58.

EXAMINER

Shouxiang Shu

DATE CONSIDERED

4/14/03

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		Ramdani et al.	
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EXAMINER INITIAL		DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
SK	AA	5 2 7 0 2 9 8	12/14-93	Ramesh	505	1	8/4/92
	AB	5 4 1 8 3 8 9	5/23/95	Watanabe	257	295	11/9/93
	AC	5 2 4 8 5 6 4	9/28/93	Ramesh	428	688	12/9/92
	AD	5 1 5 5 6 5 8	10/13/92	Inam et al.	361	321	3/5/92
	AE	6 0 5 5 1 7 9	4/25/00	Koganei et al.	365	158	5/17/99
	AF	5 3 2 6 7 2 1	7/5/94	Summerfelt	437	131	5/1/92
	AG	5 3 1 0 7 0 7	5/10/94	Oishi et al.	501	126	9/28/92
	AH	4 9 9 9 8 4 2	3/12/91	Huang et al.	372	45	3/1/89
	AI	5 8 7 4 8 6 0	2/23/99	Brunel et al.	330	285	12/4/96
	AJ	6 0 0 2 3 7 5	12/14/99	Corman et al.	343	853	9/2/97
	AK	4 8 8 2 3 0 0	11/21/89	Inoue et al.	437	236	10/6/88
	AL	5 6 7 4 3 6 6	10/7/97	Hayashi et al.	204	298.09	6/7/95
	AM	5 7 3 1 2 2 0	3/24/98	Tsu et al.	437	60	6/7/95
	AN	5 8 2 8 0 8 0	10/27/98	Yano et al.	257	43	8/17/95
	AO	5 8 0 1 1 0 5	9/1/98	Yano et al.	438	785	6/14/96

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

SK	AP	"Optimizing GMR Spin Valves: The Outlook for Improved Properties", W. F. Enghoff et al., 1998 Int'l NonVolatile Memory Technology Conference, pp. 34-37.
	AQ	"Processing and Performance of Piezoelectric Films", Y. Wang et al., Univ. of MD, Wilcoxon Research Co., and Motorola Labs.
	AR	"Nonlinear acoustoelectric interactions in GaAs/LiNbO ₃ structures", M. Rotter et al., 1999 American Institute of Physics, pp. 965-967.
	AS	"Surface acoustic wave propagation on lead zirconate titanate thin films", K. Sreenivas et al., App. Phys. Lett. 52(9), 29 February 1988, pp. 709-711.
	AT	"Single Chip fused hybrids for acousto-electric and acousto-optic applications", M. Rotter et al., 1997 American Institute of Physics, pp. 2097-2099.
	AU	"Surface Acoustic Wave Propagation in PZT/YBCO/SrTiO ₃ and PbTi O ₃ /YBCO/SrTiO ₃ Epitaxial Heterostructures", Dept. of Physics & Astrophysics, Univ. of Delhi, pp. 275-283.
	AV	"Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", S. Mathews et al., American Association for the Advancement of Science, 1997, pp.238-240.

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Form PTO 142
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

205890US99

SERIAL NO.

09/721,566

APPLICANT

Jamal Ramdani et al.

FILING DATE

November 22, 2000

GROUP

2811

LIST OF REFERENCES CITED BY APPLICANT

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>SPC</i>	AA	5,270,298	12/14/93	Ramesh			
<i>SPC</i>	AB	5,556,463	09/17/96	Guenzer			
<i>SPC</i>	AC	5,741,724	04/21/98	Ramdani et al.			
<i>SPC</i>	AD	6,103,403	08/15/00	Grigorian et al.			
<i>SPC</i>	AE	6,113,690	09/05/00	Yu et al.			
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	05-048072	02/26/93	Japan w/English Abstract		
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	
	AX	
	AY	
	AZ	

☐ Additional References sheet(s) attached

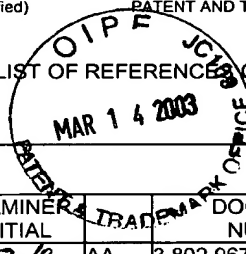
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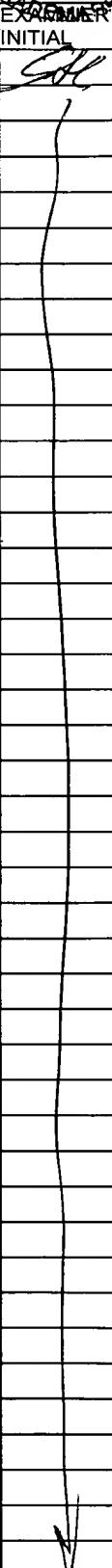
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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 205890US99		SERIAL NO. 09/721,566	
LIST OF REFERENCES CITED BY APPLICANT 				APPLICANT Jamal Ramdani et al.			
				FILING DATE November 22, 2000		GROUP 2811	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	TRADE MARK	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Ede</i>		AA 3,802,967	04/09/74	Ladany et al.			
		AB 4,174,422	11/13/79	Matthews et al.			
		AC 4,404,265	09/13/83	Manasevit			
		AD 4,482,906	11/13/84	Hovel et al.			
		AE 4,523,211	06/11/85	Morimoto et al.			
		AF 4,661,176	04/28/87	Manasevit			
		AG 4,793,872	12/27/88	Meunier et al.			
		AH 4,846,926	07/11/89	Kay et al.			
		AJ 4,855,249	08/08/89	Akasaki et al.			
		AI 4,891,091	01/02/90	Shastri			
		AK 4,912,087	03/27/90	Aslam et al.			
		AL 4,928,154	05/22/90	Umeno et al.			
		AM 4,963,949	10/16/90	Wanlass et al.			
		AN 5,141,894	08/25/92	Bisaro et al.			
		AQ 5,159,413	10/27/92	Calviello et al.			
		AP 5,173,474	12/22/92	Connell et al.			
		AQ 5,221,367	06/22/93	Chisholm et al.			
		AR 5,225,031	07/06/93	McKee et al.			
		AS 5,358,925	10/25/94	Neville Connell et al.			
		AT 5,393,352	02/28/95	Summerfelt			
		AU 5,418,216	05/23/95	Fork			
		AV 5,450,812	09/19/95	McKee et al.			
		AW 5,478,653	12/26/95	Guenzer			
		AX 5,482,003	01/09/96	McKee et al.			
		AY 5,514,484	05/07/96	Nashimoto			
		AZ 5,556,463	09/17/96	Guenzer			
		BA 5,588,995	12/31/96	Sheldon			
		BB 5,670,798	09/23/97	Schetzina			
		BC 5,733,641	03/31/98	Fork et al.			
		BD 5,735,949	04/07/98	Manti et al.			
		BE 5,741,724	04/21/98	Ramdani et al.			
		BF 5,810,923	09/22/98	Yano et al.			
		BG 5,830,270	11/03/98	McKee et al.			
		BH 5,912,068	06/15/99	Jia			
		BI 6,020,222	02/01/00	Wollesen			
		BJ 6,045,626	04/04/00	Yano et al.			
		BK 6,064,078	05/16/00	Northrup et al.			
		BL 6,064,092	05/16/00	Park			
		BM 6,096,584	08/01/00	Ellis-Monaghan et al.			
		BN 6,103,008	08/15/00	McKee et al.			
		BO 6,136,666	10/24/00	So			
		BP 6,174,755	01/16/01	Manning			
		BQ 6,180,486	01/30/01	Leobandung et al.			

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LIST OF REFERENCES CITED BY APPLICANT MAR 14 2003 PATENT & TRADEMARK OFFICE 6015				APPLICANT Jamal Ramdani et al			
				FILING DATE November 22, 2000		GROUP 2811	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
SK	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijail et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
	DQ	6,222,654	04/24/01	Frigo			

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
EY	5,828,080	10/27/98	Yano et al.				
EZ	5,858,814	01/12/99	Goossen et al.				
FA	5,861,966	01/19/99	Ortel				
FB	5,883,996	03/16/99	Knapp et al.				
FC	5,995,359	11/30/99	Klee et al.				
FD	6,058,131	05/02/00	Pan				
FE	6,137,603	10/24/00	Henmi				
FF	6,146,906	11/14/00	Inoue et al.				
FG	6,173,474	01/16/01	Conrad				
FH	6,180,252	01/30/01	Farrell et al.				
FI	4,242,595	12/30/0	Lehovec				
FJ	4,398,342	08/16/83	Pitt et al.				
FK	4,424,589	01/03/84	Thomas et al.				
FL	4,876,208	10/24/89	Gustafson et al.				
FM	4,482,422	11/84	McGinn et al.				
FN	4,667,088	05/19/87	Kramer				
FO	4,772,929	09/20/88	Manchester et al.				
FP	4,841,775	06/27/89	Ikeda et al.				
FQ	4,845,044	07/04/89	Ariyoshi et al.				

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SHE	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirrung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
HG	5,512,773	04/96	Wolf et al.				
HH	5,515,047	05/07/96	Yamakido et al.				
HI	5,515,810	05/14/96	Yamashita et al.				
HJ	5,519,235	05/96	Ramesh				
HK	5,549,977	08/96	Jin et al.				
HL	5,551,238	09/03/96	Prueitt				
HM	5,552,547	09/03/96	Shi				
HN	5,589,284	12/31/96	Summerfelt et al.				
HO	5,602,418	02/11/97	Imai et al.				
HP	5,633,724	05/27/97	King et al.				

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SA	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohori			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
	IX	5,872,493	02/16/99	Ella			
	IY	5,879,956	03/99	Seon et al.			
	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Partin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
	JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			
	JG	5,987,011	11/16/99	Toh			
	JH	6,022,140	02/08/00	Fraden et al.			
	JI	6,022,410	02/08/00	Yu et al.			
	JJ	6,023,082	02/08/00	McKee et al.			
	JK	6,028,853	02/22/00	Haartsen			
	JL	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al			
	JN	6,088,216	07/00	Laibowitz et al.			
	JO	6,090,659	07/00	Laibowitz et al.			
	JP	6,107,721	08/22/00	Lakin			
	JQ	6,153,010	11/28/00	Kiyoku et al			

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KA		6,153,454	11/28/00	Krivokapic			
KB		6,191,011	02/01	Gilboa et al			
KC		6,204,737	03/20/01	Ella			
KD		6,224,669	05/01/01	Yi et al.			
KE		6,225,051	05/01/01	Sugiyama et al.			
KF		6,241,821	06/05/01	Yu et al.			
KG		6,265,749	07/24/01	Gardner et al.			
KH		6,313,486	11/01	Kencke et al.			
KI		6,316,832	11/13/01	Tsuzuki et al.			
KJ		2002/0008234	01/02	Emrick			
KK		3,670,213	06/13/72	Nakawaga et al.			
KL		4,756,007	07/05/88	Qureshi et al.			
KM		4,773,063	09/20/88	Hunsperger et al.			
KN		5,394,489	02/28/95	Koch			
KO		5,406,202	04/11/95	Mehrgardt et al.			
KP		5,528,067	06/18/96	Farb et al.			
KQ		5,572,052	11/05/96	Kashihara et al.			
KR		5,767,543	06/16/98	Ooms et al.			
KS		6,175,497	01/16/01	Tseng et al.			
KT		6,197,503	03/06/01	Vo-Dinh et al.			
KU		6,248,459	06/19/01	Wang et al.			
KV		6,252,261	06/26/01	Usui et al.			
KW		6,255,198	07/03/01	Linthicum et al.			
KX		6,268,269	07/31/01	Lee et al.			
KY		6,291,319	09/18/01	Yu et al.			
KZ		6,316,785	11/13/01	Nunoue et al.			
LA		6,343,171	01/29/02	Yoshimura et al.			
LB		4,965,649	10/23/90	Zanio et al.			
LC		6,253,649	05/01	Kawahara et al.			
LD		6,211,096	04/01	Allman et al.			
LE		6,239,449	05/29/01	Fafard et al.			
LF		2001/0013313	08/16/01	Droopad et al.			
LG		6,184,044	02/06/01	Sone et al.			
LH		6,011,646	01/04/00	Mirkarimi et al.			
LI		5,227,196	07/13/93	Itoh			
LJ		6,150,239	11/21/00	Goesele et al.			
LK		5,441,577	08/15/95	Sasaki et al.			
LL		4,459,325	07/10/84	Nozawa et al.			
LM		4,392,297	07/12/83	Little			
LN		4,289,920	09/15/81	Hovel			
LO		5,281,834	01/25/94	Cambou et al.			
LP		4,901,133	02/13/90	Curran et al.			
LQ		5,514,904	05/07/96	Onga et al.			

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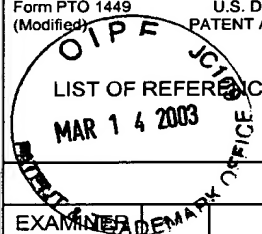
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MA	5,553,089	09/03/96	Seki et al.			
MB	5,528,057	06/18/96	Yanagase et al.			
MC	6,229,159	05/08/01	Suzuki			
MD	4,748,485	05/31/88	Vasudev			
ME	4,984,043	01/08/91	Vinal			
MF	5,754,319	05/19/98	Van De Voorde et al.			
MG	6,108,125	08/22/00	Yano			
MH	5,073,981	12/17/91	Giles et al.			
MI	5,140,651	08/18/92	Soref et al.			
MJ	5,610,744	03/11/97	Ho et al.			
MK	6,362,017	03/26/02	Manabe et al.			
ML	6,242,686	06/05/01	Kishimoto et al.			
MM	5,689,123	11/18/97	Major et al.			
MN	5,670,800	09/23/97	Nakao et al.			
MO	5,067,809	11/26/91	Tsubota			
MP	5,596,205	01/21/97	Reedy et al.			
MQ	6,175,555	01/16/01	Hoole			
MR	5,357,122	10/18/94	Okubora et al.			
MS	4,084,130	04/11/78	Holton			
MT	6,093,302	07/25/00	Montgomery			
MU	6,372,813	04/16/02	Johnson et al.			
MV	5,608,046	03/04/97	Cook et al.			
MW	5,955,591	09/21/99	Imbach et al.			
MX	6,022,963	02/08/00	McGall et al.			
MY	6,083,697	07/04/00	Beecher et al.			
MZ	5,063,081	11/05/91	Cozzette et al.			
NA	5,479,317	12/26/95	Ramesh			
NB	5,306,649	04/26/94	Hebert			
NC	5,962,069	10/05/99	Schindler et al.			
ND	5,541,422	07/30/96	Wolf et al.			
NE	5,873,977	02/23/99	Desu et al.			
NF	5,538,941	07/23/96	Findikoglu et al.			
NG	6,046,464	04/04/00	Schetzina			
NH	6,235,145	05/22/01	Li et al.			
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NK	6,348,373 B1	02/19/02	Ma et al.			
NL	6,339,664 B1	01/15/02	Farjady et al.			
NM	4,439,014	03/27/84	Stacy et al.			
NN	4,889,402	12/26/89	Reinhart			
NO	5,963,291	10/05/99	Wu et al.			
NP	6,011,641	01/04/00	Shin et al.			
NQ	6,340,788 B1	01/22/02	King et al.			

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OK	OA 5,807,440	09/15/98	Kubota et al.				
	OB 4,681,982	07/21/87	Yoshida				
	OC 4,629,821	12/16/86	Bronstein-Bonte et al.				
	OD 4,452,720	06/05/84	Harada et al.				
	OE 3,935,031	01/27/76	Adler				
	OF 5,760,426	06/02/98	Marx et al.				
	OG 5,053,835	10/01/91	Horikawa et al.				
	OH 6,326,645 B1	12/04/01	Kadota				
	OI 5,770,887	06/23/98	Tadatomo et al.				
	OJ 6,372,356 B1	04/16/02	Thornton et al.				
	OK 4,774,205	09/27/88	Choi et al.				
	OL 6,359,330 B1	03/19/02	Goudard				
	OM 5,312,765	05/17/94	Kanber				
	ON 5,734,672	03/31/98	McMinn et al.				
	OO 6,367,699 B2	04/09/02	Ackley				
	OP 5,530,235	06/25/96	Stefik et al.				
	OQ 5,623,552	04/22/97	Lane				
	OR 5,481,102	01/02/96	Hazelrigg, Jr.				
	OS 6,134,114	10/17/00	Ungermann et al.				
	OT 5,984,190	11/16/99	Nevill				
	OU 5,789,733	08/04/98	Jachimowicz et al.				
	OV 5,753,300	05/19/98	Wessels et al.				
	OW 6,208,453	03/27/01	Wessels et al.				
	OX 5,886,867	03/23/99	Chivukula et al.				
	OY 5,028,976	07/02/91	Ozaki et al.				
	OZ 5,869,845	02/09/99	Vander Wagt et al.				
	PA 5,596,214	01/21/97	Endo				
	PB 6,391,674 B2	05/21/02	Ziegler				
	PC 6,275,122 B1	08/14/01	Speidell et al.				
	PD 6,238,946 B1	05/29/01	Ziegler				
	PE 6,210,988 B1	04/03/01	Howe et al.				
	PF 6,392,257	05/21/02	Ramdani et al.				
	PG 4,442,590	04/17/84	Stockton et al.				
	PH 5,603,764	02/18/97	Matsuda et al.				
	PI 6,087,681	06/11/00	Shakuda				
	PJ 5,132,648	07/21/92	Trinh et al.				
	PK 6,427,066	07/30/02	Grube				
	PL 2002/0072245	06/13/02	Ooms et al.				
	PM 6,278,138 B1	08/21/01	Suzuki				
	PN 5,888,296	03/30/99	Ooms et al.				
	PO 5,198,269	03/30/93	Swartz et al.				
	PP 2002/0030246	03/14/02	Eisenbeiser et al.				
	PQ 2002/0047143	04/25/02	Ramdani et al.				

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<i>JP</i>	QA	5,776,359	07/07/98	Schultz et al.			
	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
	QQ	5,780,311	07/14/98	Beasom et al.			
	QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
	QS	5,399,898	03/21/95	Rostoker			
	QT	6,271,619	08/07/01	Yamada et al.			
QU	5,334,556	08/02/94	Guldi				
QV	4,910,164	03/20/90	Shichijo				
QW	4,952,420	08/28/90	Walters				
QX	6,121,647	09/19/00	Yano et al.				
QY	6,306,668 B1	10/23/01	McKee et al.				
QZ	6,143,366	11/07/00	Lu				
RA	6,410,941	06/25/02	Taylor et al.				
RB	5,397,428	03/14/95	Stoner et al.				
RC	6,432,546 B1	08/13/02	Ramesh et al.				
RD	6,345,424	02/12/02	Hasegawa et al.				
RE	6,338,756 B2	01/15/02	Dietze				
RF	5,516,725	05/14/96	Chang et al.				
RG	4,667,212	05/19/87	Nakamura				
RH	5,629,534	05/13/97	Inuzuka et al.				
RI	3,914,137	10/21/75	Huffman et al.				
RJ	5,753,928	05/19/98	Krause				
RK	5,977,567	11/02/99	Verdiell				
RL	5,130,762	07/14/92	Kulick				
RM	5,621,227	04/15/97	Joshi				
RN	6,389,209 B1	05/14/02	Suhir				
RO	5,163,118	11/10/92	Lorenzo et al.				
RP	5,926,493	07/20/99	O'Brien et al.				
RQ	5,323,023	06/21/94	Fork				

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SA	6,156,581	12/05/00	Vaudo et al.				
SB	5,395,663	03/07/95	Tabata et al.				
SC	4,146,297	03/27/79	Alferness et al.				
SD	5,452,118	09/19/95	Maruska				
SE	5,889,296	03/30/99	Imamura et al.				
SF	6,300,615 B1	10/09/01	Shinohara et al.				
SG	6,232,910 B1	05/15/01	Bell et al.				
SH	5,686,741	11/11/97	Ohori et al.				
SI	4,959,702	09/25/90	Moyer et al				
SJ	6,100,578	08/08/00	Suzuki				
SK	6,410,947 B1	06/25/02	Wada				
SL	6,417,059 B2	07/09/02	Huang				
SM	6,461,927 B1	10/08/02	Mochizuki et al.				
SN	6,462,360 B1	10/08/02	Higgins, Jr. et al.				
SO	5,981,976	11/09/99	Murasato				
SP	5,981,980	11/09/99	Miyajima et al.				
SQ	2002/0006245 A1	01/17/02	Kubota et al.				
SR	2002/0131675 A1	09/19/02	Litvin				
SS	6,256,426 B1	07/03/01	Duchet				
ST	6,278,523 B1	08/21/01	Gorecki				
SU	6,319,730 B1	11/20/01	Ramdani et al.				
SV	6,404,027	06/11/02	Hong et al.				
SW	6,312,819 B1	11/06/01	Jia et al.				
SX	5,119,448	06/02/92	Schaefer et al.				
SY	4,120,588	10/17/78	Chaum				
SZ	5,194,917	03/16/93	Regener				
TA	5,018,816	05/28/91	Murray et al.				
TB	5,953,468	09/14/99	Finnila et al.				
TC	5,561,305	10/01/96	Smith				
TD	5,896,476	04/20/99	Wisseman et al.				
TE	4,934,777	06/19/90	Jou et al.				
TF	6,320,238 B1	11/20/01	Kizilyalli et al.				
TG	6,393,167 B1	05/21/02	Davis et al.				
TH	5,760,427	06/02/98	Onda				
TI	6,411,756 B2	06/25/02	Sadot et al.				
TJ	5,668,048	09/16/97	Kondo et al.				
TK	5,852,687	12/22/98	Wickham				
TL	5,122,852	06/16/92	Chan et al.				
TM	5,173,835	12/22/92	Cornett et al.				
TN	5,055,835	10/08/91	Sutton				
TO	6,139,483	10/31/00	Seabaugh et al.				
TP	5,283,462	02/01/94	Stengel				
TQ	6,103,403	08/15/00	Grigorian et al.				

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	UB	5,427,988	06/27/95	Sengupta et al.			
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	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
	UJ	5,995,528	11/30/99	Fukunaga et al.			
	UK	5,075,743	12/24/91	Behfar-Rad			
	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
	UO	6,278,137 B1	08/21/01	Shimoyama et al.			
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	UR	6,194,753 B1	02/27/01	Seon et al.			
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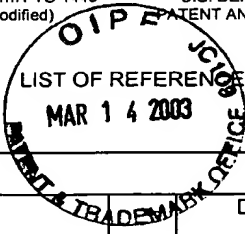
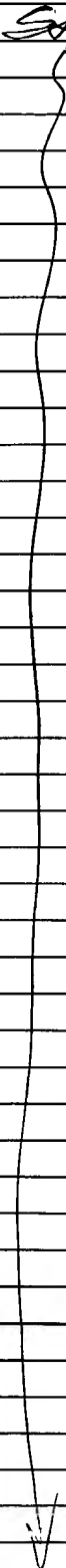
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	AAD	0 602 568	06/22/94	EP	X	
	AAE	0 607 435	07/27/94	EP	X	
	AAF	1 001 468	05/17/00	EP	X	
	AAG	0 514 018	11/19/92	EP	X	
	AAH	0 999 600	05/10/00	EP	X	
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	AAK	11-238683	08/31/99	Japan	X	
	AAL	11-260835	09/24/99	Japan w/English Abstract	X	
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	AAN	5-48072	02/26/93	Japan w/English Abstract	X	
	AAO	52-88354	07/23/77	Japan w/English Abstract	X	
	AAP	54-134554	10/19/79	Japan w/English Abstract	X	
	AAQ	55-87424	07/02/80	Japan w/English Abstract	X	
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	AAS	6-232126	08/19/94	Japan	X	
	AAT	6-291299	10/18/94	Japan w/English Abstract	X	
	AAU	63-34994	02/15/88	Japan w/English Abstract	X	
	AAV	63-131104	06/03/88	Japan w/English Abstract	X	
	AAW	63-198365	08/17/88	Japan w/English Abstract	X	
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	AAY	6-334168	12/02/94	Japan	X	
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	ABA	WO 99/14804	03/25/99	WIPO	X	
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	ABE	WO 00/48239	08/17/00	WIPO		
	ABF	WO 99/14797	03/25/99	WIPO		
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	ABN	3-41783	02/91	Japan (English Abstract only)		
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Jamal Ramdani et al

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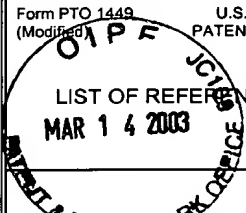
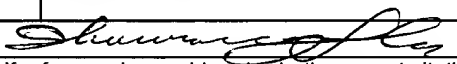
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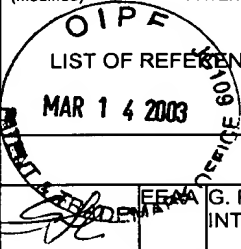

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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	CCAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO ₃ Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.					
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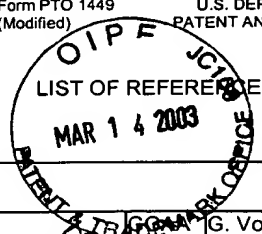
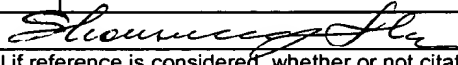
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		FILING DATE November 22, 2000	GROUP 2811
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EEAL	Philip BALL; "The Next Generation of Optical Fibers"; <i>Technology Review</i> , May 2001; pp.55-61		
EEAM	John D. JOANNOPOULOS, et al.; "Molding the Flow of Light"; <i>Photonic Crystals</i> ; Princeton University Press, 1995		
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EEAO	G. H. JIN, et al.; "PLZT Film Waveguide Mach-Zehnder Electrooptic Modulator"; <i>Journal of Lightwave Technology</i> , Vol. 18, No. 6, June 2000; pp.807-812		
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	FFAA	Lucent Technologies, Inc. "Arrayed Waveguide Grating Multiplexer/Demultiplexer"; January 2000; 4 pages					
	FFAB	Hisashi SHICHIJO, et al.; "Co-Integration of GaAs MESFET and Si CMOS Circuits"; IEEE ELECTRON DEVICE LETTERS, VOL. 9, NO. 9, SEPTEMBER 1988; pp.444-446					
	FFAC	H. SHICHIJO, et al.; "GaAs MESFET and Si CMOS Cointegration and Circuit Techniques"; 1988 IEEE; GaAs IC Symposium - 239-242					
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GGAB		G. Vogg et al.; "Epitaxial alloy films of zintl-phase $\text{Ca}(\text{Si}_{1-x}\text{Ge}_x)_2$ "; Journal of Crystal Growth 223 (2001); pp. 573-576					
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